

## **INCHANGE SEMICONDUCTOR**

# **isc Silicon NPN Power Transistor**

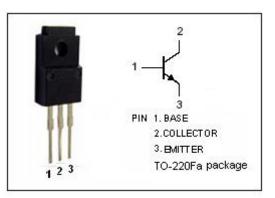
# 2SC3627

#### DESCRIPTION

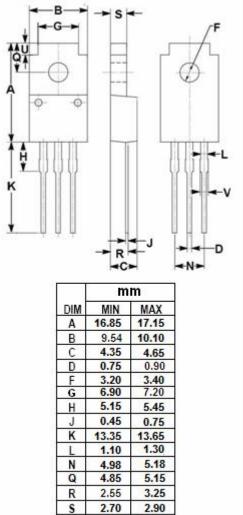
- · High Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 200V(Min)
- · High Switching Speed
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

- · Switching regulator and high voltage switching applications
- · High speed DC-DC converter applications



#### ABSOLUTE MAXIMUM RATINGS(Ta=25℃) SYMBOL VALUE UNIT PARAMETER 250 Collector-Base Voltage V Vсво $V_{\text{CEO}}$ Collector-Emitter Voltage 200 V **Emitter-Base Voltage** 7 $V_{\text{EBO}}$ V Collector Current-Continuous lc 10 А Collector Current-Peak 15 Ісм **Base Current-Continuous** 2 А I<sub>R</sub> **Collector Power Dissipation** 2 @ Ta=25℃ Pc W **Collector Power Dissipation** 30 @ T<sub>C</sub>=25°C ТJ °C Junction Temperature 150 Storage Temperature Range -55~150 °C Tstg



### isc website: www.iscsemi.com 1 isc & iscsemi is registered trademark

U

v

1.75

1.30

2.05

1.50



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1.0

μs

### ELECTRICAL CHARACTERISTICS

#### $T_{\texttt{C}}\text{=}25^{\circ}\!\!\mathbb{C}$ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	200			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>E</sub> = 0	250			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 200V ; I <sub>E</sub> = 0			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V ; I <sub>C</sub> = 0			1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 10mA ; V <sub>CE</sub> = 5V	15			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 5V	20		80	
Switching T	ïmes		1		I	
tr	Rise Time				1.0	μ <b>S</b>
t <sub>stg</sub>	Storage Time	I <sub>B1</sub> = -I <sub>B2</sub> = 0.6A, V <sub>CC</sub> ≈ 150V, R <sub>L</sub> = 25 Ω ; P <sub>W</sub> = 20 μ s; Duty≤1%			2.5	μ <b>S</b>

Notice:

tf

Fall Time

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